Three quadrant triacs high commutation

BTA216X series C

GENERAL DESCRIPTION

Glass passivated high commutation triacs in a plastic envelope intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

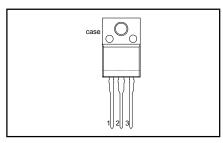
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM}	BTA216X- Repetitive peak off-state voltages	500C 500	600C 600	800C 800	V
I _{T(RMS)} I _{TSM}	RMS on-state current Non-repetitive peak on-state current	16 140	16 140	16 140	A A

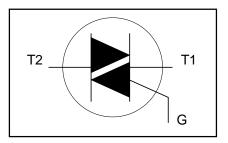
PINNING - SOT186A

PIN	DESCRIPTION	
1	main terminal 1	
2	main terminal 2	
3	gate	
case	isolated	

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
V_{DRM}	Repetitive peak off-state voltages		-	-500 500 ¹	-600 600 ¹	-800 800	V
I _{T(RMS)}	RMS on-state current	full sine wave;	-		16		Α
I _{TSM}	Non-repetitive peak on-state current	$T_{mb} \le 38 ^{\circ}\text{C}$ full sine wave; $T_{j} = 25 ^{\circ}\text{C}$ prior to surge $t = 20 ^{\circ}\text{ms}$	-		140		A
l l ² t	I ² t for fusing	t = 16.7 ms t = 10 ms	-		150 98		A A ² s
dl _⊤ /dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 20 \text{ A}; I_{G} = 0.2 \text{ A}; $ $dI_{G}/dt = 0.2 \text{ A}/\mu\text{s}$			100		A/μs
I _{GM}	Peak gate current		-		2 5		A
V_{GM}	Peak gate voltage Peak gate power		-		5 5		l V W
P _{GM} P _{G(AV)}	Average gate power	over any 20 ms period	-		0.5		W
$T_{stg} \ T_{j}$	Storage temperature Operating junction temperature	ponou	-40 -		150 125		သိ

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 $A/\mu s$.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction to heatsink	full or half cycle with heatsink compound without heatsink compound	-	-	4.0 5.5	K/W K/W
$R_{th j-a}$	Thermal resistance junction to ambient	in free air	-	55	-	K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current ²	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$				
		T2+ G		18	35	mA
		T2+ G		21	35	mA
		T2- G-	2	34	35	mA
I _L	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$				
-		T2+ G	+ -	-	20	mA
		T2+ G	· -	-	30	mA
		T2- G-	-	-	20	mA
l _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	-	15	mA
$V_{T}^{I_{H}}$	On-state voltage	$I_{T} = 20 \text{ A}$	-	1.2	1.5	V
V _{GT}	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	0.7	1.5	V
-	1	$ V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_i = 125 \text{ °C}$	0.25	0.4	-	V
I_D	Off-state leakage current	$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C}$ $V_D = V_{DRM(max)}; T_j = 125 \text{ °C}$	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	V _{DM} = 67% V _{DRM(max)} ; T _j = 125 °C; exponential waveform; gate open circuit	1000	1	V/μs
dl _{com} /dt	Critical rate of change of commutating current	V _{DM} = 400 V; T _j = 125 °C; I _{T(RMS)} = 16 A; without snubber; gate open circuit	3	14	A/ms
t _{gt}	Gate controlled turn-on time	$I_{TM} = 20 \text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1 \text{ A}$; $dI_G/dt = 5 \text{ A}/\mu\text{s}$	1	2	μs

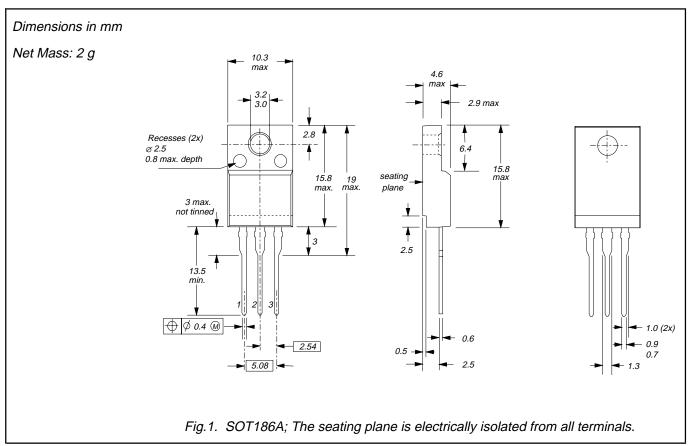
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² Device does not trigger in the T2-, G+ quadrant.

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MECHANICAL DATA



- Refer to mounting instructions for F-pack envelopes.
 Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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